~ L N	umber Hit	s Search Text	DB	Time stamp
4		1 (semiconduct\$3 same (defect\$3 and (resist	USPAT;	2004/01/08 17:22
		or photoresist or photopolymer\$7) and	US-PGPUB;	
1		develop\$4)) and (HMDS or	EPO; JPO;	
		hexamethyldisilazane or hexamethyl adj	IBM TDB	
		disilazane or silazane) same prim\$3	_	
5		3 (((semiconduct\$3 or silicon or "Si" or	USPAT;	2004/01/08 17:31
		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM_TDB	
		or photopolymer\$7) same (develop\$4 or		
}		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or spin\$4 or rotat\$3		
		or turn\$3) same (exhaust\$3 or air or gas		
		or sweep\$ or flow\$3 or pass\$3) near5	:	
		(velocit\$3 or speed\$3)	*	
6	4	2 (((((resist or photoresist or	USPAT;	2004/01/08 19:51
		photopolymer\$7) same (develop\$4 or rins\$3	US-PGPUB;	
		or clean\$3 or remov\$3 or residue or	EPO; JPO;	
		rubbish or debris) same (spin\$4 or spun or	IBM_TDB	
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		<pre>speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or</pre>		
		residue) and (resist or photoresist or		
		photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7)		
		same (develop\$4 or rins\$3) same (spin\$4 or		·
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or gas or		
İ		sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3))) and		
		(semiconduct\$3 or wafer or silicon or		
		"Si")) and (spin\$4 or spun or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or sweep\$3		
		or swept or inert or gas\$4)) and (resist		
		or photoresist or photopolym\$7) same		
		(prim\$3 or pre adj treat\$3 or pretreat\$3)		
7	9	7 (((resist or photoresist or	USPAT;	2004/01/08 19:53
		photopolymer\$7) and (semiconduct\$3 or	US-PGPUB;	
		silicon or "Si" or wafer or substrate)	EPO; JPO;	
		same (HMDS or hexamethyldisilazane or	IBM_TDB	
		hexamethyl adj disilazane) same (prim\$3 or		
		pretreat\$4 or pre adj treat\$4)) not		
		((semiconduct\$3 same (defect\$3 and (resist		
		or photoresist or photopolymer\$7) and		
		develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyldisilazane		
		disilazane or silazane) same prim\$3)) and		
		(((HMDS or hexamethyldisilazane or		
		hexamethyl adj disilazane or silazane) or		
		prim\$3) near5 vapor) same (seconds or		
		"sec")		
L				L

8 15	or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:05
	flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)))) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm")		
9	1 (semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:11
10	(((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 20:16
11	4 (("6613500") or ("6486072") or ("6222936") or ("5985497")).PN.	USPAT; US-PGPUB; EPO; JPO;	2004/01/08 20:34
22	6 semiconduct\$3 and HMDS with prim\$3	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/06/19 18:13
_ 200	5 semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/06/20 08:26
- 624	<pre>(semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3 (semiconduct\$3 or silicon or "Si" or</pre>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 17:22
- 624	wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)	US-PGPUB; EPO; JPO; IBM_TDB	2003/00/20 09:03

				1-2
_	1152	((semiconduct\$3 or silicon or "Si" or	USPAT;	2003/06/20 09:21
		<pre>wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7)</pre>	US-PGPUB; EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM TDB	
		or photopolymer\$7) same (develop\$4 or	TBI1_TBB	
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3		
		or speed\$3)		
_	12	(((semiconduct\$3 or silicon or "Si" or	USPAT;	2003/06/20 09:10
		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM_TDB	1
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3		
		or speed\$3)) and ((develop\$4 or rins\$3) or		
		(spin\$4 or rotat\$3 or turn\$3 or speed\$3)) same (exhaust\$3 or air) near5 (velocit\$3		
		or speed\$3)		
_	130		USPAT;	2003/06/20 09:22
	150	wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM_TDB	
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)		0004/01/00 17 01
_	11	(((semiconduct\$3 or silicon or "Si" or	USPAT;	2004/01/08 17:31
		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO; IBM TDB	
		and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or	IBM_IBB	
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or spin\$4 or rotat\$3		
		or turn\$3) same (exhaust\$3 or air or gas		
		or sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3)		
	1347	((semiconduct\$3 or silicon or "Si" or	USPAT;	2003/06/20 09:21
:		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
	}	(resist or photoresist or photopolymer\$7)	EPO; JPO; IBM TDB	
		and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or	IBM_IDD	
		rins\$3 or clean\$3 or dry\$3) same (spin\$4		Į
		or rotat\$3 or turn\$3 or speed\$3)		
_	179	((semiconduct\$3 or silicon or "Si" or	USPAT;	2003/06/20 09:22
		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM_TDB	
		or photopolymer\$7) same (develop\$4 or		
		rins\$3 or clean\$3 or dry\$3) same (spin\$4		
		or rotat\$3 or turn\$3) near5 (velocit\$3 or		
	11	speed\$3) (((semiconduct\$3 or silicon or "Si" or	USPAT;	2003/10/15 15:31
_	11	wafer) same ((defect\$3 or residue) and	US-PGPUB;	2303, 20, 10 10.01
	1	(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM TDB	
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3)		
		specurs)	L	I

				0000/06/00
-	1091	((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or	USPAT; US-PGPUB;	2003/06/20 17:12
		remov\$3 or residue or rubbish or debris)	EPO; JPO;	
		same (spin\$4 or spun or rotat\$3 or turn\$3)	IBM TDB	
		near5 (velocit\$3 or speed\$3)) not	_	
		((((semiconduct\$3 or silicon or "Si" or		
		wafer) same ((defect\$3 or residue) and		
		(resist or photoresist or photopolymer\$7)		
		and develop\$4)) and (resist or photoresist		
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or	:	
		speed\$3))	8	
_	825	(((resist or photoresist or	USPAT;	2003/06/20 17:15
		photopolymer\$7) same (develop\$4 or rins\$3	US-PGPUB;	
		or clean\$3 or remov\$3 or residue or	EPO; JPO;	
		rubbish or debris) same (spin\$4 or spun or	IBM_TDB	
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) not ((((semiconduct\$3 or silicon		
		or "Si" or wafer) same ((defect\$3 or		
		residue) and (resist or photoresist or		
		photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or		
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or gas or		
		sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3))) and		
		(semiconduct\$3 or wafer or silicon or		
		"Si")		
_	320	((((resist or photoresist or	USPAT;	2003/06/20 17:18
		photopolymer\$7) same (develop\$4 or rins\$3	US-PGPUB;	
		or clean\$3 or remov\$3 or residue or	EPO; JPO;	
		rubbish or debris) same (spin\$4 or spun or	IBM TDB	
		rotat\$3 or turn\$3) near5 (velocit\$3 or	_	
		speed\$3)) not ((((semiconduct\$3 or silicon		
		or "Si" or wafer) same ((defect\$3 or		
		residue) and (resist or photoresist or		
1	0.0	photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7)		
		same (develop\$4 or rins\$3) same (spin\$4 or		
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or gas or		
		sweep\$ or flow\$3 or pass\$3) near5	1	
		(velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or		
		(semiconducts) or water of silicon of "Si")) and (spin\$4 or spun or rotat\$3 or		
		turn\$3) same (exhaust\$3 or air or sweep\$3		
		or swept or inert or gas\$4)		
1	j	Of Shope of friend of gastif	1	l

39	(((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or syn\$4 or rotat\$3 or syn\$5 or syn\$6 o	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 19:50
1	(velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) ("4556785").PN.	USPAT; US-PGPUB	2003/06/21 16:17
443	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 19:53
237		USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:06
85	hexamethyl adj disilazane or silazane) or prim\$3) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/08 19:53

Г	6097	((resist or photoresist or photopolymer\$7)	USPAT;	2003/06/23 16:57
_	0057	same ((develop\$4) and (rins\$3 or wash\$3 or	US-PGPUB;	
		same ((develops4) and (lines or mubble)		
		clean\$3 or remov\$3 or residue or rubbish	EPO; JPO;	
		or debris)) same (spin\$4 or spun or	IBM_TDB	
		rotat\$3 or turn\$3)) not (((((resist or		
		photoresist or photopolymer\$7) same		
		(develop\$4 or rins\$3 or clean\$3 or remov\$3		
		or residue or rubbish or debris) same		
		(spin\$4 or spun or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) not		
		((((semiconduct\$3 or silicon or "Si" or		
		((((Semiconducts) of Silicon of Si of		Į.
		wafer) same ((defect\$3 or residue) and		
		(resist or photoresist or photopolymer\$7)		
		and develop\$4)) and (resist or photoresist		
		or photopolymer\$7) same (develop\$4 or		
. }		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
, 1		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3))) and (semiconduct\$3 or wafer or		
		silicon or "Si")) and (spin\$4 or spun or		
		Silicon of Si // and (Spinya of Span of		
		rotat\$3 or turn\$3) same (exhaust\$3 or air		
		or sweep\$3 or swept or inert or gas\$4))		
		and (resist or photoresist or		
		photopolym\$7) same (prim\$3 or pre adj		
		treat\$3 or pretreat\$3))		
	701		USPAT;	2003/06/23 16:56
-	721		1	
-	121	photoresist or photopolymer\$7) same	US-PGPUB;	
_	721	photoresist or photopolymer\$7) same	1 .	
_	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or	US-PGPUB;	
_	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish	US-PGPUB; EPO; JPO;	
_	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or	US-PGPUB; EPO; JPO;	
-	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or	US-PGPUB; EPO; JPO;	
_	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same	US-PGPUB; EPO; JPO;	
_	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3	US-PGPUB; EPO; JPO;	
_	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same	US-PGPUB; EPO; JPO;	
_	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3)	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7)	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3)	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or turn\$3)	US-PGPUB; EPO; JPO;	
	/21	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or sweept or inert or gas\$4))	US-PGPUB; EPO; JPO;	
	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or	US-PGPUB; EPO; JPO;	
	721	photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not ((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or sweept or inert or gas\$4))	US-PGPUB; EPO; JPO;	

	1 4 1	(430/311,326-327,329.ccls. and (((resist	USPAT;	2004/01/08 20:04
-	141	or photoresist or photopolymer\$7) same	US-PGPUB;	2004/01/08 20.04
			EPO; JPO;	
		((develop\$4) and (rins\$3 or wash\$3 or	4	
		clean\$3 or remov\$3 or residue or rubbish	IBM_TDB	
		or debris)) same (spin\$4 or spun or		
		rotat\$3 or turn\$3)) not (((((resist or		
		photoresist or photopolymer\$7) same		
		(develop\$4 or rins\$3 or clean\$3 or remov\$3		
		or residue or rubbish or debris) same		
		(spin\$4 or spun or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) not	-	
		((((semiconduct\$3 or silicon or "Si" or		
		wafer) same ((defect\$3 or residue) and		
		(resist or photoresist or photopolymer\$7)		i i
		and develop\$4)) and (resist or photoresist		
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and	1	
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3))) and (semiconduct\$3 or wafer or		
		silicon or "Si")) and (spin\$4 or spun or		
		rotat\$3 or turn\$3) same (exhaust\$3 or air		
		or sweep\$3 or swept or inert or gas\$4))		
		and (resist or photoresist or		
		photopolym\$7) same (prim\$3 or pre adj		
		treat\$3 or pretreat\$3)))) and (rins\$3 or		
		wash\$3 or clean\$3 or remov\$3 or residue or		
	}			
		rubbish or debris) same (revolution or		
		"rpm")	HCDAM	2004/01/00 20:11
-	10	(semiconduct\$3 same (defect\$3 and (resist	USPAT;	2004/01/08 20:11
		or photoresist or photopolymer\$7) and	US-PGPUB;	
		develop\$4)) and (HMDS or	EPO; JPO;	
		hexamethyldisilazane or hexamethyl adj	IBM_TDB	
1		disilazane or silazane) same prim\$3		0004/01/00 00 10
-	11	(((semiconduct\$3 or silicon or "Si" or	USPAT;	2004/01/08 20:12
		wafer) same ((defect\$3 or residue) and	US-PGPUB;	
		(resist or photoresist or photopolymer\$7)	EPO; JPO;	
		and develop\$4)) and (resist or photoresist	IBM_TDB	
	I .	or photopolymer\$7) same (develop\$4 or		
	'	rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3)		
	<u> </u>	speea>3)	I	l

-	40	(((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3	USPAT;	2003/10/15 15:35
		or clean\$3 or remov\$3 or residue or	US-PGPUB; EPO; JPO;	
		rubbish or debris) same (spin\$4 or spun or	IBM TDB	
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) not ((((semiconduct\$3 or silicon		
		or "Si" or wafer) same ((defect\$3 or		
		residue) and (resist or photoresist or		
		photopolymer\$7) and develop\$4)) and		
		(resist or photoresist or photopolymer\$7)		
		same (develop\$4 or rins\$3) same (spin\$4 or		
		rotat\$3 or turn\$3) near5 (velocit\$3 or		
		speed\$3)) and (develop\$4 or rins\$3 or		
		clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or		
		sweep\$ or flow\$3 or pass\$3) near5		
		(velocit\$3 or speed\$3))) and		
		(semiconduct\$3 or wafer or silicon or		
		"Si")) and (spin\$4 or spun or rotat\$3 or		
•		turn\$3) same (exhaust\$3 or air or sweep\$3		
1		or swept or inert or gas\$4)) and (resist		
		or photoresist or photopolym\$7) same		
1		(prim\$3 or pre adj treat\$3 or pretreat\$3)		
-	86	(((resist or photoresist or	USPAT;	2003/10/15 15:37
		photopolymer\$7) and (semiconduct\$3 or	US-PGPUB;	
		silicon or "Si" or wafer or substrate)	EPO; JPO;	
		same (HMDS or hexamethyldisilazane or	IBM_TDB	
		hexamethyl adj disilazane) same (prim\$3 or		
		pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist		
		or photoresist or photopolymer\$7) and		1
		develop\$4)) and (HMDS or		
		hexamethyldisilazane or hexamethyl adj		
		disilazane or silazane) same prim\$3)) and	1	
		(((HMDS or hexamethyldisilazane or		
		hexamethyl adj disilazane or silazane) or		
		prim\$3) near5 vapor) same (seconds or		
	4.0	"sec")		
-	148	(430/311,326-327,329.ccls. and (((resist	USPAT;	2003/10/15 15:55
		or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or	US-PGPUB; EPO; JPO;	
		clean\$3 or remov\$3 or residue or rubbish	IBM TDB	
		or debris)) same (spin\$4 or spun or	1511_155	
		rotat\$3 or turn\$3)) not (((((resist or		
		photoresist or photopolymer\$7) same		
		(develop\$4 or rins\$3 or clean\$3 or remov\$3		
		or residue or rubbish or debris) same		
		(spin\$4 or spun or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) not		
		((((semiconduct\$3 or silicon or "Si" or		
		wafer) same ((defect\$3 or residue) and		
		(resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist		
		or photopolymer\$7) same (develop\$4 or		
		rins\$3) same (spin\$4 or rotat\$3 or turn\$3)		
		near5 (velocit\$3 or speed\$3)) and		
.		(develop\$4 or rins\$3 or clean\$3 or dry\$3		
,		or spin\$4 or rotat\$3 or turn\$3) same		
		(exhaust\$3 or air or gas or sweep\$ or		
		flow\$3 or pass\$3) near5 (velocit\$3 or		
		speed\$3))) and (semiconduct\$3 or wafer or		
		silicon or "Si")) and (spin\$4 or spun or		
		rotat\$3 or turn\$3) same (exhaust\$3 or air		
		or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or		
		and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj		
		treat\$3 or pretreat\$3)))) and (rins\$3 or		
		wash\$3 or clean\$3 or remov\$3 or residue or		
		rubbish or debris) same (revolution or		
		"rpm")		
j !				